

[a step for] preparing a [couple of, or] first laser assembly and a second laser assembly by repeating the laser assembly forming step;

[a step for] bringing the first laser assembly and the second laser assembly into registration with each other so that the first electrode and the second electrode of the first laser assembly are brought to opposition to the second electrode and the first electrode of the second laser assembly with a fusing material interposed therebetween;

[a step for] intimately attaching the first laser assembly and the second laser assembly [assemblies] with each other and melting the fusing material to bond the first laser assembly and the second laser assembly [assemblies] with each other;

[a step for] removing at least the substrate of an insulating property from the first laser assembly and the second laser assembly [assemblies]; and

[a step for] forming an electrode on the bottom of the n-type semiconductor layer of the first laser assembly and the second laser assembly [assemblies].

8. (Amended) The method of fabricating a semiconductor laser device according to claim 7, wherein [the step for] bringing the first laser assembly and the second laser assembly into registration includes [a step for] supplying a fusing material onto at least either of the first electrode of the first laser assembly or the second electrode of the second laser assembly, and [a step for] supplying a fusing material onto at least either of the second electrode of the first laser assembly or the first electrode of the second laser assembly.

10. (Amended) The method of fabricating a semiconductor laser device according to claim 9, wherein the substrate is made of sapphire, and [the] removing [step is a step of] at least the substrate comprises irradiating laser light of a wavelength of 200 to 300 nm from the back side of the substrate.

Add the following new claims 11-17:

7-11 The semiconductor laser device according to claim 3, wherein at least one of the connecting layers has a Schottky barrier.

8 12. The semiconductor laser device according to claim 2, wherein at least one of the first laser unit and the second laser unit has a Schottky barrier between the p-side electrode and the p-type semiconductor layer.

9 13. The semiconductor laser device according to claim 3, wherein at least one of the first laser unit and the second laser unit has a Schottky barrier between the p-side electrode and the p-type semiconductor layer.

14. A semiconductor laser device according to claim 2, wherein at least one of the first laser unit and the second laser unit is a semiconductor laser having a gallium nitride (GaN) system semiconductor deposited.

15. A semiconductor laser device according to claim 3, wherein at least one of the first laser unit and the second laser unit is a semiconductor laser having a gallium nitride (GaN) system semiconductor deposited.

16. A semiconductor laser device according to claim 4, wherein at least one of the first laser unit and the second laser unit is a semiconductor laser having a gallium nitride (GaN) system semiconductor deposited.

17. A semiconductor laser device according to claim 5, wherein at least one of the first laser unit and the second laser unit is a semiconductor laser having a gallium nitride (GaN) system semiconductor deposited.--

Handwritten notes and stamps on the left margin:  
- "Sub C-1" (top)  
- "X2" and "Cmpd." (middle)  
- "Sub C-1" (bottom)  
- A vertical stamp: "RECEIVED" (top to bottom)  
- A date stamp: "MAR 1 2000" (bottom)